

## **AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

### **Listing of Claims:**

1        1. (Currently amended) A method for measuring alignment between a first  
2 semiconductor die and a second semiconductor die, comprising:

3              applying a pattern of voltage signals to a two-dimensional array of  
4 conductive transmitter elements that form a transmitter array on the first  
5 semiconductor die;

6              wherein the transmitter array on the first semiconductor die is located over  
7 a corresponding two-dimensional array of conductive receiver elements that form  
8 a receiver array on the second semiconductor die;

9              wherein transmitter elements have a different spacing than receiver  
10 elements, whereby a two-dimensional vernier alignment structure is created when  
11 the transmitter array is located over the receiver array;

12             wherein a voltage signal applied to a transmitter element induces a voltage  
13 signal in one or more receiver elements;

14             amplifying voltage signals induced in receiver elements in the receiver  
15 array; and

16             analyzing the amplified signals to determine an alignment between the  
17 first semiconductor die and the second semiconductor die.

1        2 (Canceled).

1        3. (Original) The method of claim 1,

2           wherein the transmitter array is organized as a two-dimensional  $n \times m$  grid  
3   including  $nm$  conductive elements; and  
4           wherein the receiver array includes at least three conductive elements  
5   which are not collinear.

1           4. (Original) The method of claim 1,  
2           wherein the receiver array is organized as a two-dimensional  $n \times m$  grid  
3   including  $nm$  conductive elements; and  
4           wherein the transmitter array includes at least three conductive elements  
5   which are not collinear.

1           5. (Original) The method of claim 1, wherein determining the alignment  
2   involves determining six degrees of alignment, including:  
3           an  $x$  alignment parallel to plane of the receiver array;  
4           a  $y$  alignment parallel to plane of the receiver array and normal to the  $x$   
5   axis;  
6           a  $z$  alignment normal to the plane of the receiver array;  
7           an angular alignment,  $\theta$ , about the  $z$  axis;  
8           an angular alignment,  $\Psi$ , about the  $y$  axis; and  
9           an angular alignment,  $\Phi$ , about the  $x$  axis.

1           6. (Original) The method of claim 5, wherein determining the alignment  
2   involves analyzing coupling capacitances between individual receiver elements  
3   and individual transmitter elements to determine the  $x$  alignment, the  $y$  alignment  
4   and the angular alignment,  $\theta$ .

1        7. (Original) The method of claim 6, wherein analyzing the coupling  
2    capacitances involves determining a nearest neighbor mapping between receiver  
3    elements and transmitter elements.

1        8. (Original) The method of claim 5, wherein determining the alignment  
2    involves using a mapping function generated by a three-dimensional capacitance  
3    field solver simulation to determine the z alignment, the angular alignment,  $\Psi$ , and  
4    the angular alignment,  $\Phi$ .

1        9. (Original) The method of claim 5, wherein determining the z alignment,  
2    the angular alignment,  $\Psi$ , and the angular alignment,  $\Phi$ , involves summing  
3    capacitances between individual receiver elements in the receiver array and all  
4    transmitter elements in the transmitter array, thereby effectively considering the  
5    transmitter array to be one large plate.

1        10. (Original) The method of claim 5, wherein determining the z  
2    alignment, the angular alignment,  $\Psi$ , and the angular alignment,  $\Phi$ , involves  
3    summing capacitances between individual transmitter elements in the transmitter  
4    array and all receiver elements in the receiver array, thereby effectively  
5    considering the receiver array to be one large plate.

1        11. (Original) The method of claim 1, further comprising electrically  
2    varying the pitch of the transmitter array by grouping together adjacent transmitter  
3    elements.

1        12. (Original) The method of claim 1, further comprising electrically  
2    varying the pitch of the receiver array by grouping together adjacent receiver  
3    elements.

1       13. (Original) The method of claim 1, wherein transmitter elements and  
2 receiver elements are:

3           square;  
4           rectangular;  
5           hexagonal;  
6           triangular;  
7           oval; or  
8           round.

1       14. (Original) The method of claim 1,  
2           wherein transmitter elements are located in a metal layer of the first  
3 semiconductor die and are not covered by higher layers of metal; and  
4           wherein receiver elements are located in a metal layer of the second  
5 semiconductor die and are not covered by higher layers of metal.

1       15. (Currently amended) An apparatus that measures alignment between a  
2 first semiconductor die and a second semiconductor die, comprising:

3           a two-dimensional array of conductive transmitter elements that form a  
4 transmitter array on the first semiconductor die;

5           a two-dimensional array of conductive receiver elements that form a  
6 receiver array on the second semiconductor die;;

7           wherein transmitter elements have a different spacing than receiver  
8 elements, whereby a two-dimensional vernier alignment structure is created when  
9 the transmitter array is located over the receiver array;

10          a driving mechanism configured to apply a pattern of voltage signals to the  
11 transmitter array;

12 wherein a voltage signal applied to a transmitter element induces a voltage  
13 signal in one or more receiver elements when the transmitter array is located over  
14 the receiver array;

15 an amplification mechanism configured to amplify voltage signals induced  
16 in receiver elements in the receiver array; and

17 an analysis mechanism configured to analyze the amplified signals to  
18 determine an alignment between the first semiconductor die and the second  
19 semiconductor die.

1 16 (Canceled).

1 17. (Original) The apparatus of claim 15,  
2 wherein the transmitter array is organized as a two-dimensional  $n \times m$  grid  
3 including  $nm$  conductive elements; and  
4 wherein the receiver array includes at least three conductive elements  
5 which are not collinear.

1 18. (Original) The apparatus of claim 15,  
2 wherein the receiver array is organized as a two-dimensional  $n \times m$  grid  
3 including  $nm$  conductive elements; and  
4 wherein the transmitter array includes at least three conductive elements  
5 which are not collinear.

1 19. (Original) The apparatus of claim 15, wherein the driving mechanism  
2 and the analysis mechanism are configured to determine six degrees of alignment,  
3 including:  
4 an  $x$  alignment parallel to plane of the receiver array;

5           a  $y$  alignment parallel to plane of the receiver array and normal to the  $x$   
6 axis;  
7           a  $z$  alignment normal to the plane of the receiver array;  
8           an angular alignment,  $\theta$ , about the  $z$  axis;  
9           an angular alignment,  $\Psi$ , about the  $y$  axis; and  
10          an angular alignment,  $\Phi$ , about the  $x$  axis.

1           20. (Original) The apparatus of claim 19, wherein the analysis mechanism  
2 is configured to determine coupling capacitances between individual receiver  
3 elements and individual transmitter elements to determine the  $x$  alignment, the  $y$   
4 alignment and the angular alignment,  $\theta$ .

1           21. (Original) The apparatus of claim 20, wherein the analysis mechanism  
2 is configured to determine a nearest neighbor mapping between receiver elements  
3 and transmitter elements.

1           22. (Original) The apparatus of claim 19, wherein the analysis mechanism  
2 is configured to use a mapping function generated by a three-dimensional  
3 capacitance field solver simulation to determine the  $z$  alignment, the angular  
4 alignment,  $\Psi$ , and the angular alignment,  $\Phi$ .

1           23. (Original) The apparatus of claim 19, wherein the apparatus is  
2 configured to determine the  $z$  alignment, the angular alignment,  $\Psi$ , and the angular  
3 alignment,  $\Phi$ , by summing capacitances between individual receiver elements in  
4 the receiver array and all transmitter elements in the transmitter array, thereby  
5 effectively considering the transmitter array to be one large plate.

1           24. (Original) The apparatus of claim 19, wherein the apparatus is  
2 configured to determine the  $z$  alignment, the angular alignment,  $\Psi$ , and the angular  
3 alignment,  $\Phi$ , by summing capacitances between individual transmitter elements  
4 in the transmitter array and all receiver elements in the receiver array, thereby  
5 effectively considering the receiver array to be one large plate.

1           25. (Original) The apparatus of claim 15, wherein the apparatus is  
2 configured to electrically vary the pitch of the transmitter array by grouping  
3 together adjacent transmitter elements.

1           26. (Original) The apparatus of claim 15, wherein the apparatus is  
2 configured to electrically vary the pitch of the receiver array by grouping together  
3 adjacent receiver elements.

1           27. (Original) The apparatus of claim 15, wherein transmitter elements and  
2 receiver elements are:

3           square;  
4           rectangular;  
5           hexagonal;  
6           triangular;  
7           oval; or  
8           round.

1           28. (Original) The apparatus of claim 15,  
2           wherein transmitter elements are located in a metal layer of the first  
3 semiconductor die and are not covered by higher layers of metal; and  
4           wherein receiver elements are located in a metal layer of the second  
5 semiconductor die and are not covered by higher layers of metal.